

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
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TYPE : 6PC16C3N1T**

CHIP SIZE	0.36 * 0.36 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	119,000 pcs

Maximum Ratings(Ta=25°C)

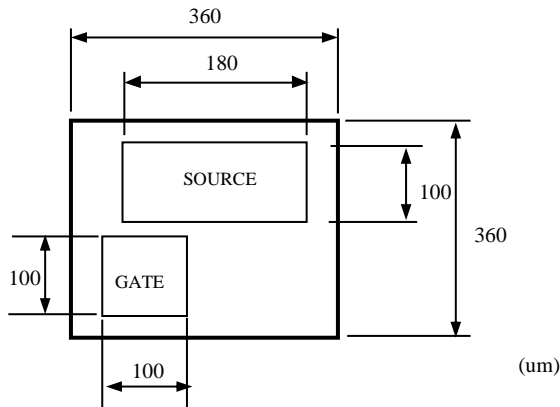
Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	30	V
Gate-source voltage	VGSS	±8	V
Drain Current (DC)	ID	0.3	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS1			±500	nA	VGS=±8V VDS=0V
2	IDSS			10	uA	VDS=32V VGS=0V
3	BVDSS	32			V	ID=100uA
4	VTH	0.55		1.05	V	ID=250uA
5	RDS(on)		1.2	2.0	Ω	VGS=4.0V ID=100mA
6	Yfs	180			mS	VDS=10V Id=100mA

※ Built-in ZD between Gate and Source. ESD Protected : 2000V



NOTE: